

wherein said second semiconductor chip is a DRAM chip, and said third semiconductor chip is a logic chip.

4. (Twice Amended) A semiconductor device comprising:

a semiconductor chip consisting of [at least either a circuit against static damage or a passive component, wherein said semiconductor chip consists of] only a [said] passive component, said passive component includes all of a resistor, a capacitor and a reactor.

6. (Amended) The semiconductor device according to claim 1 [5], wherein

said second semiconductor chip and said third semiconductor chip include no circuits against static damage.

REMARKS

Claims 1-4, 6 and 9-22 are pending in the present application. Claims 9-22 stand allowed and claims 1 and 4 stand rejected. Claims 2, 3 and 6 are indicated as having allowable subject matter but are objected to for depending from a rejected base claim. In particular, claim 1 stands rejected under the second paragraph of 35 USC §112 and claim 4 stands rejected under 35 USC §102 as anticipated by Ohashi et al.

In response, Applicants have amended claim 1 by clarifying that the "said semiconductor chip" refers to the earlier recited second semiconductor chip. Claim 6 has been amended to depend from claim 1 instead of the previously cancelled claim 5. In view of these amendments, Applicants urge that rejection under 35 USC §112 ¶2 of claim

1 and the objection to claim 6 have been overcome as well as the objections to claims 2 and 3.

Claim 4 stands rejected under 35 USC § 102 as anticipated by Ohashi et al. The Examiner asserts that the PFC circuit 110 includes a reactor 114, a resistor 112 and a capacitor 118 and suggests that all can be formed on a single chip. Applicants urge, however, that the referenced circuitry of Ohashi et al. does not identically correspond to every limitation recited in claim 4. Specifically, claim 4 requires that the recited semiconductor chip consist of only a passive component which includes all of a resistor, a capacitor and a reactor.

In contrast to claim 4, the PFC circuit 110 of Ohashi et al. includes a transistor switch 120 that is an active component. Thus, the PFC circuit 110 of Ohashi et al. is different from the semiconductor chip consisting of only a passive component as recited in claim 4. Applicants urge the factual determination that Ohashi et al. anticipate claim 4 is flawed and, therefore, request reconsideration and withdrawal of the rejection under 35 USC § 102 of claim 4.

Applicants note that Office Action Summary Sheet does not acknowledge priority under 35 USC 119 or receipt of the certified copies of the priority documents. Applicants included such a claim and priority documents at the time of filing on March 19, 2001. Applicants respectfully request clarification of the Official Record by acknowledging the claim to foreign priority and receipt of the priority documents.

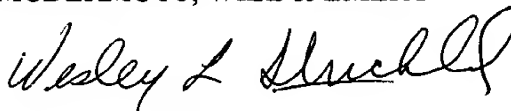
SUMMARY

In view of the above remarks and amendments, Applicants submit that all remaining claims are in condition for allowance and passage of this case to issue is respectfully requested.

To the extent necessary, a petition for an extension of time under 37 C.F.R. 1.136 is hereby made. Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

MCDERMOTT, WILL & EMERY

A handwritten signature in black ink, appearing to read "Wesley L. Strickland". The signature is fluid and cursive, with the first name "Wesley" and last name "Strickland" clearly distinguishable.

Wesley L. Strickland
Registration No. 44,363

600 13th Street, N.W.
Washington, DC 20005-3096
(202) 756-8000 WLS:
Facsimile: (202) 756-8087
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